

EMD12 / UMD12N

NPN + PNP Complex Digital Transistors (Bias Resistor Built-in Transistors) Datasheet

<For DTr1(NPN)>

Parameter	Value
V _{CC}	50V
I _{C(MAX.)}	100mA
R ₁	47kΩ
R ₂	47kΩ

<For DTr2(PNP)>

Parameter	Value
V _{CC}	-50V
I _{C(MAX.)}	-100mA
R ₁	47 k Ω
R ₂	47kΩ

Features

- 1) Both the DTC144E chip and DTA144E chip in one package.
- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit).
- The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- 4) Only the on/off conditions need to be set for operation, making the circuit design easy.
- 5) Lead Free/RoHS Compliant.

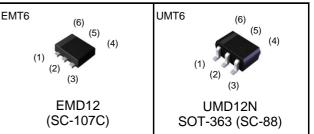
Application

Inverter circuit, Interface circuit, Driver circuit

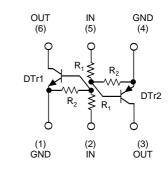
Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
EMD12	EMT6	1616	T2R	180	8	8,000	D12
UMD12N	UMT6	2021	TR	180	8	3,000	D12

Packaging specifications

●Outline



Inner circuit



●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	DTr1(NPN)	DTr2(PNP)	Unit
Supply voltage	V _{CC}	50	-50	V
Input voltage	V _{IN}	-10 to +40	-40 to +10	V
Output current	۱ _۵	30	-30	mA
Collector current	I _{C(MAX.)} *1	100	-100	mA
Power dissipation	P _D ^{*2}	150 (Total) ^{*3}		mW
Junction temperature	Tj	150		°C
Range of storage temperature	T _{stg}	-55 to +150		°C

●Electrical characteristics(Ta = 25°C) <For DTr1(NPN)>

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
	V _{I(off)}	$V_{CC} = 5V, I_{O} = 100 \mu A$	-	-	0.5	V
Input voltage	V _{I(on)}	$V_0 = 0.3V, I_0 = 2mA$	3.0	-	-	v
Output voltage	V _{O(on)}	I _O / I _I = 10mA / 0.5mA	-	0.1	0.3	V
Input current	l _i	$V_1 = 5V$	-	-	0.18	mA
Output current	I _{O(off)}	$V_{CC} = 50V, V_{I} = 0V$	-	-	0.5	μA
DC current gain	G _I	$V_0 = 5V, I_0 = 5mA$	68	-	-	-
Input resistance	R ₁	-	32.9	47	61.1	kΩ
Resistance ratio	R_2/R_1	-	0.8	1	1.2	-
Transition frequency	f _T *1	$V_{CE} = 10V, I_E = -5mA$ f = 100MHz	-	250	-	MHz

•Electrical characteristics(Ta = 25°C) <For DTr2(PNP)>

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input voltage	V _{I(off)}	$V_{CC} = -5V, I_{O} = -100 \mu A$	-	-	-0.5	V
	V _{I(on)}	$V_0 = -0.3V, I_0 = -2mA$	-3.0	-	-	v
Output voltage	V _{O(on)}	$I_0 / I_1 = -10 \text{mA} / -0.5 \text{mA}$	-	-0.1	-0.3	V
Input current	I _I	$V_1 = -5V$	-	-	-0.18	mA
Output current	I _{O(off)}	$V_{CC} = -50V, \ V_I = 0V$	-	-	-0.5	μA
DC current gain	G	$V_0 = -5V, I_0 = -5mA$	68	-	-	-
Input resistance	R ₁	-	32.9	47	61.1	kΩ
Resistance ratio	R_2/R_1	-	0.8	1	1.2	-
Transition frequency	f _T *1	V _{CE} = -10V, I _E = 5mA f = 100MHz	-	250	-	MHz

*1 Characteristics of built-in transistor

*2 Each terminal mounted on a reference footprint

*3 120mW per element must not be exceeded.

●Electrical characteristic curves (Ta = 25°C) <For DTr1(NPN)>

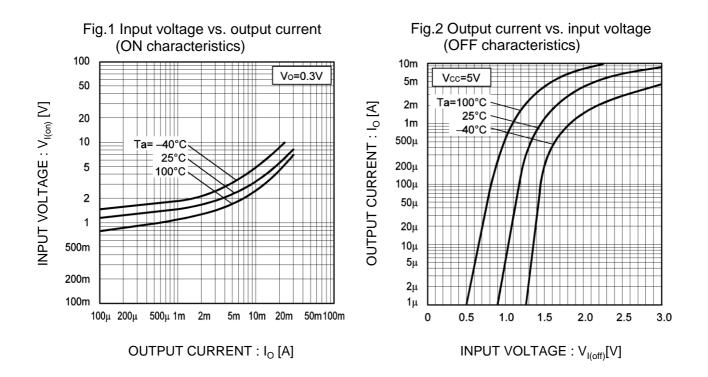
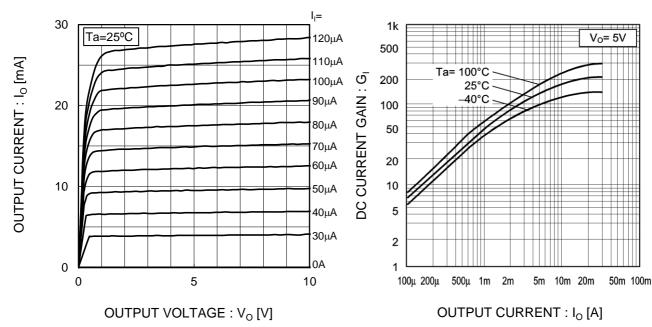


Fig.3 Output current vs. output voltage





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●Electrical characteristic curves (Ta = 25°C) <For DTr1(NPN)>

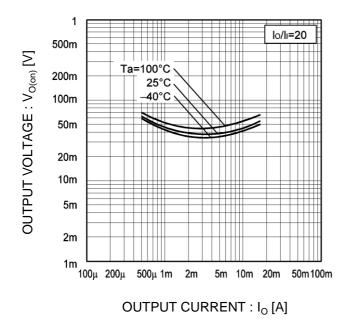
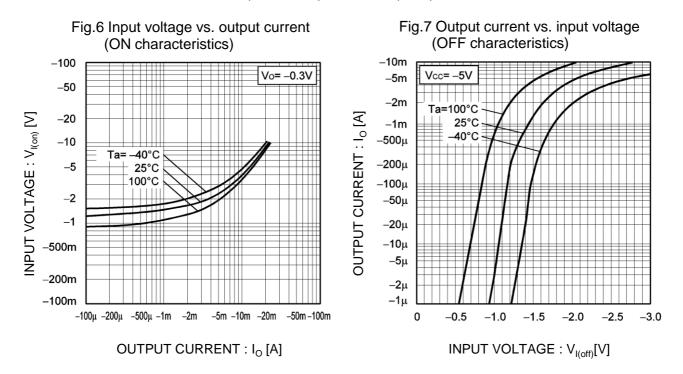


Fig.5 Output voltage vs. output current

•Electrical characteristic curves (Ta = 25°C) <For DTr2(PNP)>



●Electrical characteristic curves (Ta = 25°C) <For DTr2(PNP)>

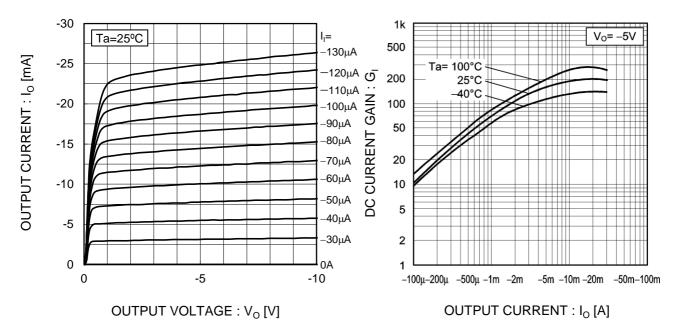
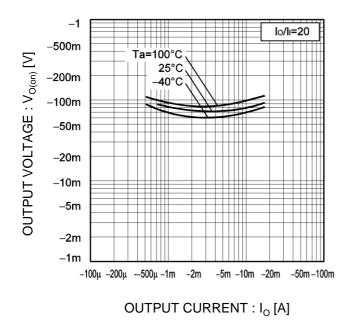


Fig.8 Output current vs. output voltage

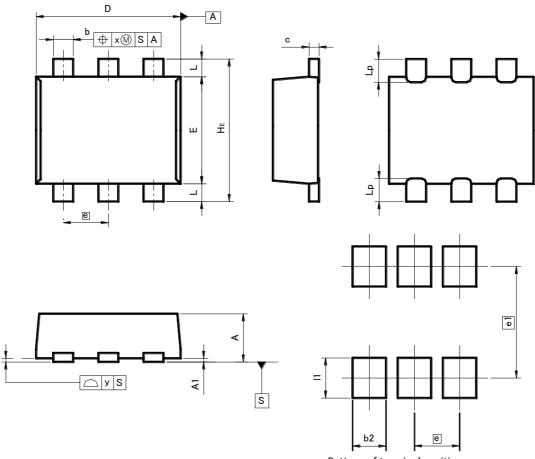
Fig.9 DC current gain vs. output current

Fig.10 Output voltage vs. output current



•Dimensions (Unit : mm)





Pattern of terminal position areas [Not a recommended pattern of soldering pads]

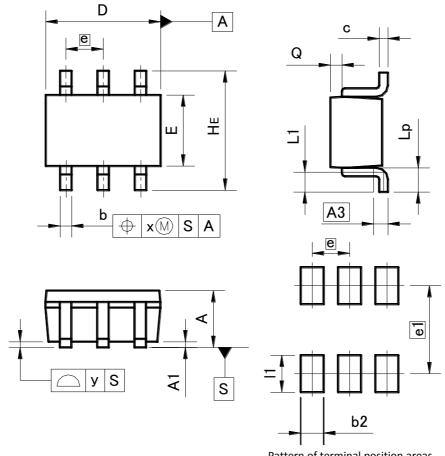
DIM	MILIMETERS		INC	HES	
DIM	MIN	MAX	MIN	MAX	
А	0.45	0.55	0.018	0.022	
A1	0.00	0.10	0.000	0.004	
b	0.17	0.27	0.007	0.011	
С	0.08	0.18	0.003	0.007	
D	1.50	1.70	0.059	0.067	
E	1.10	1.30	0.043	0.051	
е	0.	50	0.020		
HE	1.50	1.70	0.059	0.067	
L	0.10	0.30	0.004	0.012	
Lp	-	0.35	-	0.014	
х	-	0.10	-	0.004	
У	-	0.10	-	0.004	

DIM		ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
b2	-	0.37	-	0.015
e1	1.:	25	0.0	49
1	- 0.45		-	0.018

Dimension in mm / inches

•Dimensions (Unit : mm)





Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM	MILIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
A	0.80	1.00	0.031	0.039
A1	0.00	0.10	0.000	0.004
A3	0.2	25	0.0	10
b	0.15	0.30	0.006	0.012
с	0.10	0.20	0.004	0.008
D	1.90	2.10	0.075	0.083
E	1.15	1.35	0.045	0.053
е	0.	65	0.026	
HE	2.00	2.20	0.079	0.087
L1	0.20	0.50	0.008	0.020
Lp	0.25	0.55	0.010	0.022
Q	0.10	0.30	0.004	0.012
x	_	0.10	_	0.004
У	_	0.10	_	0.004

DIM		ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
b2	-	0.40	-	0.016
e1	1.	55	0.0)61
1	-	0.65	-	0.026

Dimension in mm / inches

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